



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION

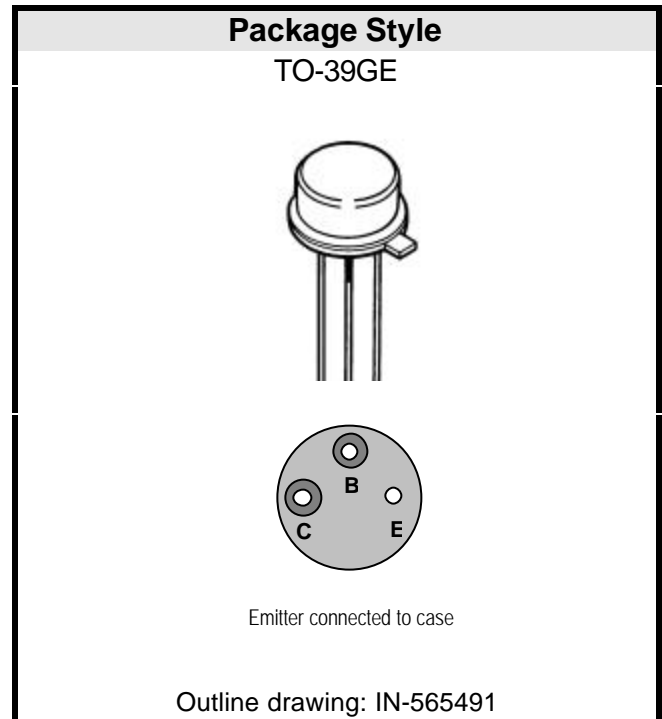
The **PMRF227** is designed for VHF class C FM power amplifier applications operating at 12.5 Volts. The grounded emitter configuration extends the useful frequency of operation to 225 MHz.

FEATURES

- Replacement for **Motorola MRF227**
- Grounded Emitter TO-39 Package
- All Gold Metalization for Enhanced Reliability

MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$

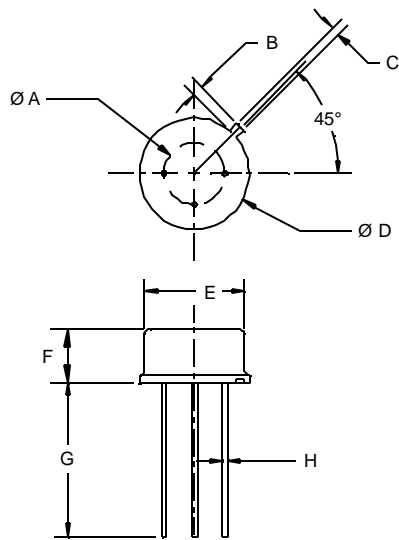
SYMBOL	RATING	UNITS
V_{CBO}	36	V
V_{CEO}	16	V
V_{EBO}	4.0	V
I_C	600	mA
P_D	5.0	W
θ_{JC}	35	$^\circ\text{C/W}$
T_{STG}	-65 to +200	$^\circ\text{C}$
T_J	+200	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 50\text{ mA}$			36			V
BV_{CEO}	$I_C = 50\text{ mA}$			16			V
BV_{EBO}	$I_E = 1\text{ mA}$			4			V
I_{CBO}	$V_{CB} = 15.0\text{ V}$					1	mA
h_{FE}	$V_{CE} = 5\text{ V}$	$I_C = 50\text{ mA}$		20		200	---
C_{OB}	$V_{CB} = 12.5\text{ V}$	$f = 1\text{ MHz}$				15	pF
$P_{G_{hc}}$	$V_{CE} = 12.5$	$P_{OUT} = 3.0\text{ W}$	$F = 225\text{ MHz}$	13.5	60		dB %

PMRF227



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.355 / 9.020	.370 / 9.370
E	.315 / 8.010	.335 / 8.500
F	.165 / 4.200	.180 / 4.570
G	.500 / 12.700	.750 / 19.050
H	.016 / 0.410	.020 / 0.508

Outline drawing: IN-565491